

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a driver circuit comprising a plurality of thin film transistors for driving said plurality of switching elements,
wherein each of said plurality of thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.
2. (Previously Presented) The active matrix display device according to claim 1 wherein said gate electrode is located over said semiconductor layer.
3. (Previously Presented) The active matrix display device according to claim 1 wherein all of said plurality of thin film transistors are p-channel transistors.
4. (Previously Presented) The active matrix display device according to claim 1 wherein all of said plurality of thin film transistors are n-channel transistors.
5. (Previously Presented) The active matrix display device according to claim 1 wherein said substrate is a glass substrate.
6. (Previously Presented) The active matrix display device according to claim 1 wherein said crystallized semiconductor layer comprises silicon.
7. (Previously Presented) An active matrix display device comprising:

a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes,
each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically
changing luminous strength disposed at each of said pixel electrodes; and
a driver circuit comprising a plurality of thin film transistors for driving said plurality
of switching elements, wherein each of said plurality of thin film transistors comprises a
crystallized semiconductor layer, a gate insulating film adjacent to said crystallized
semiconductor layer and a gate electrode adjacent to said gate insulating film,
wherein said crystallized semiconductor layer has source and drain regions and at
least one lightly doped region.

8. (Previously Presented) The active matrix display device according to claim 7
wherein said substrate is a glass substrate.

Excluded
9. (Previously Presented) The active matrix display device according to claim 7
wherein said source and drain regions and said at least one lightly doped region are doped
with phosphorus.

10. (Canceled)

11. (Previously Presented) The active matrix display device according to claim 7
wherein said gate electrode is located over said semiconductor layer.

12. (Original) The active matrix display device according to claim 7 wherein said
gate electrode is located over said semiconductor layer.

13. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes,
each of said switching elements comprising a thin film transistor;

a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and

a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor,

wherein each of said n-channel and p-channel thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.

14. (Previously Presented) The active matrix display device according to claim 13 wherein said substrate is a glass substrate.

15. (Previously Presented) The active matrix display device according to claim 13 wherein said gate electrode is located over said semiconductor layer.

16. (Previously Presented) The active matrix display device according to claim 13 wherein said crystallized semiconductor layer comprises silicon.

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17. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;

a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and

a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor, each of said first and second thin film transistors comprising a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film,

wherein said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

18. (Currently Amended) The active matrix display device according to claim 17 wherein said substrate is a glass substrate.

19. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes,
each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically
changing luminous strength disposed at each of said pixel electrodes; and
a driver circuit comprising a plurality of thin film transistors for driving said plurality
of switching elements,
wherein each of the film transistors of said switching elements and said driver circuit
comprises a crystallized semiconductor layer, a gate insulating film adjacent to said
crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.

20. (Previously Presented) The active matrix display device according to claim 19
wherein said gate electrode is located over said semiconductor layer.

21. (Previously Presented) The active matrix display device according to claim 19
wherein all of said plurality of thin film transistors are p-channel transistors.

22. (Previously Presented) The active matrix display device according to claim 19
wherein all of said plurality of thin film transistors are n-channel transistors.

23. (Previously Presented) The active matrix display device according to claim 19
wherein said substrate is a glass substrate.

24. (Previously Presented) The active matrix display device according to claim 19
wherein said crystallized semiconductor layer comprises silicon.

25. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes,
each of said switching elements comprising a thin film transistor;

a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and

a driver circuit comprising a plurality of thin film transistors for driving said plurality of switching elements,

wherein each of the thin film transistors of the switching elements and the driver circuit comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film,

wherein said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

26. (Previously Presented) The active matrix display device according to claim 25 wherein said substrate is a glass substrate.

27. (Previously Presented) The active matrix display device according to claim 25 wherein said source and drain regions and said at least one lightly doped region are doped with phosphorus.

28. (Canceled)

29. (Previously Presented) The active matrix display device according to claim 25 wherein said gate electrode is located over said semiconductor layer.

30. (Previously Presented) The active matrix display device according to claim 25 wherein said crystallized semiconductor layer comprises silicon.

31. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;

a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and

a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor,

wherein each of the film transistors of the switching elements and said n-channel and p-channel thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.

32. (Previously Presented) The active matrix display device according to claim 31 wherein said substrate is a glass substrate.

33. (Previously Presented) The active matrix display device according to claim 31 wherein said gate electrode is located over said semiconductor layer.

34. (Previously Presented) The active matrix display device according to claim 31 wherein said crystallized semiconductor layer comprises silicon.

35. (Previously Presented) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor,

wherein each of the film transistors of the switching elements and said n-channel and p-channel thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film, and said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

36. (Previously Presented) The active matrix display device according to claim 35 wherein said substrate is a glass substrate.

37. (Previously Amended) The active matrix display device according to claim 35 wherein said crystallized semiconductor layer comprises silicon.

Encl. 38. (Previously Amended) The active matrix display device according to claim 17 wherein said crystallized semiconductor layer comprises silicon.
